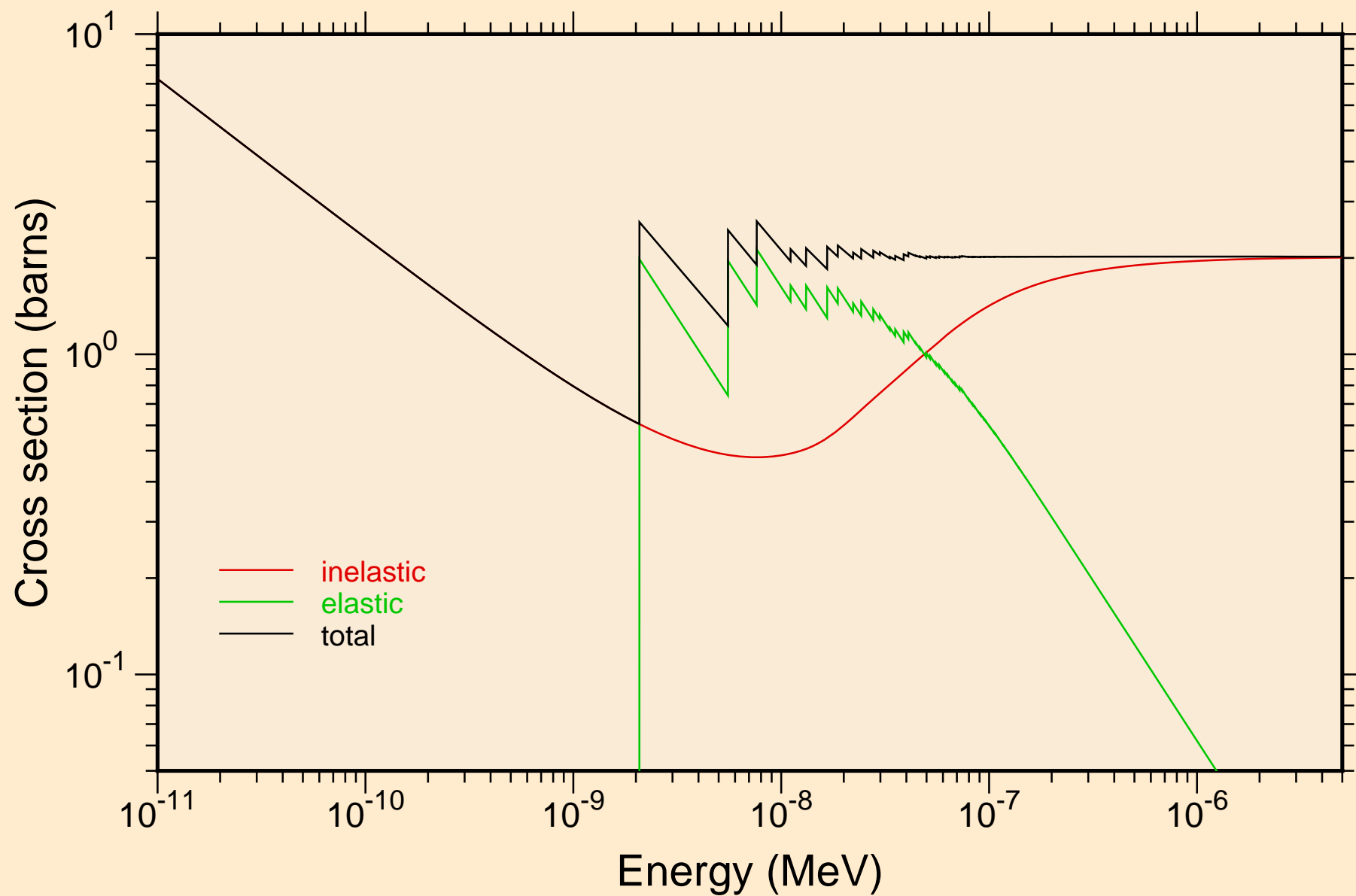
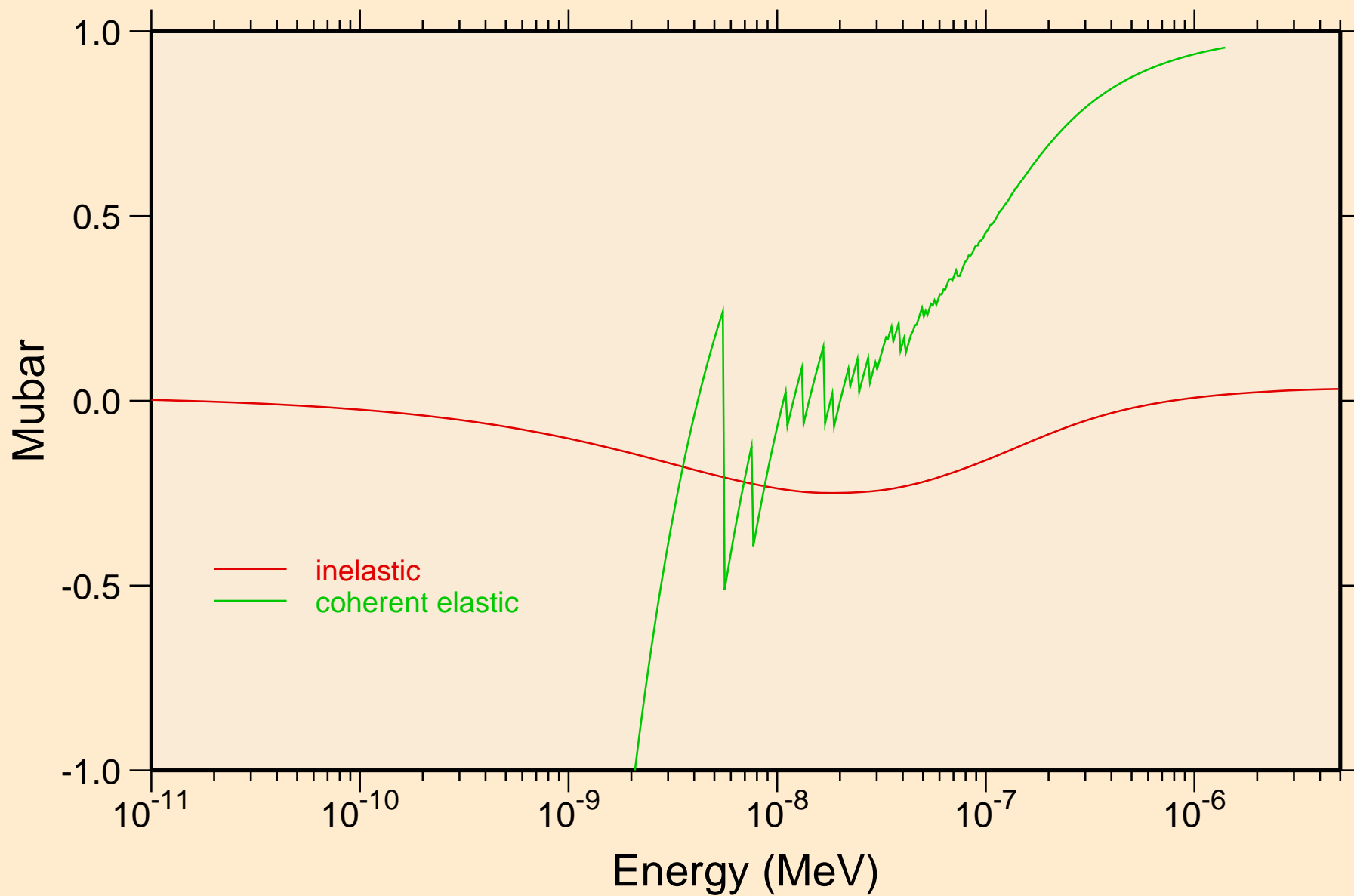


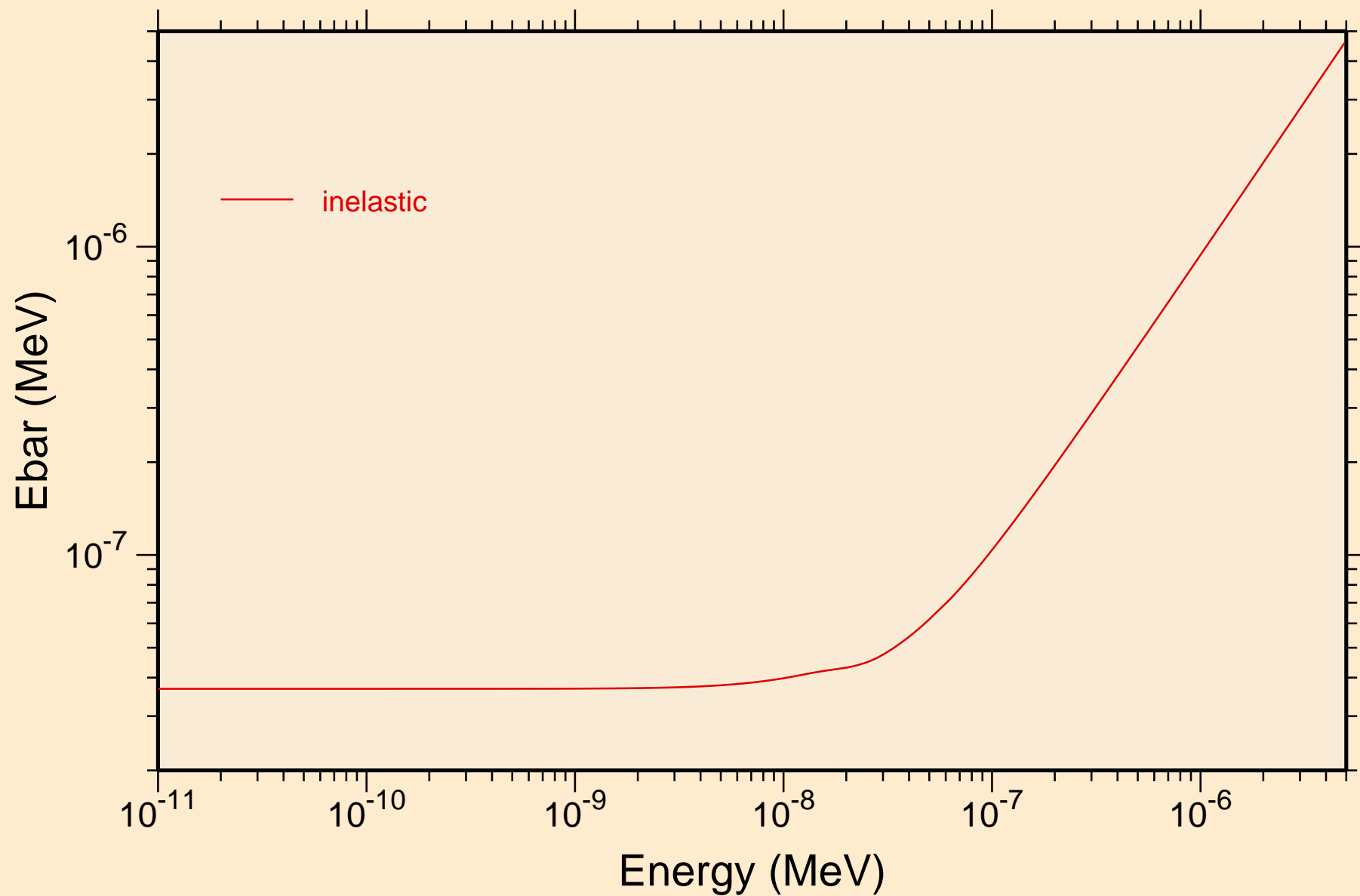
SI-SI_SG227_SILICON @ 800.00K
Thermal cross sections



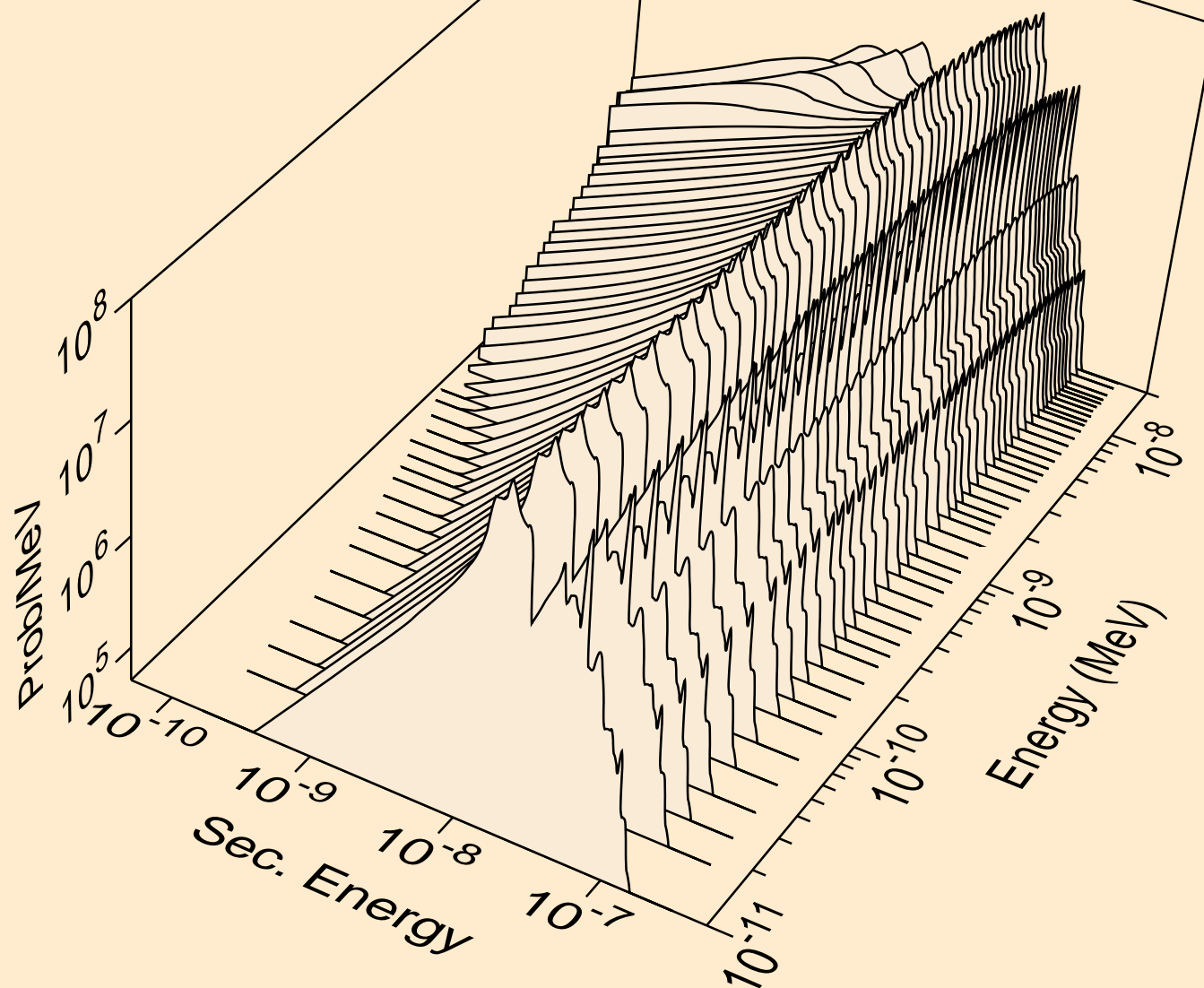
SI-SI_SG227_SILICON @ 800.00K
Thermal mubar



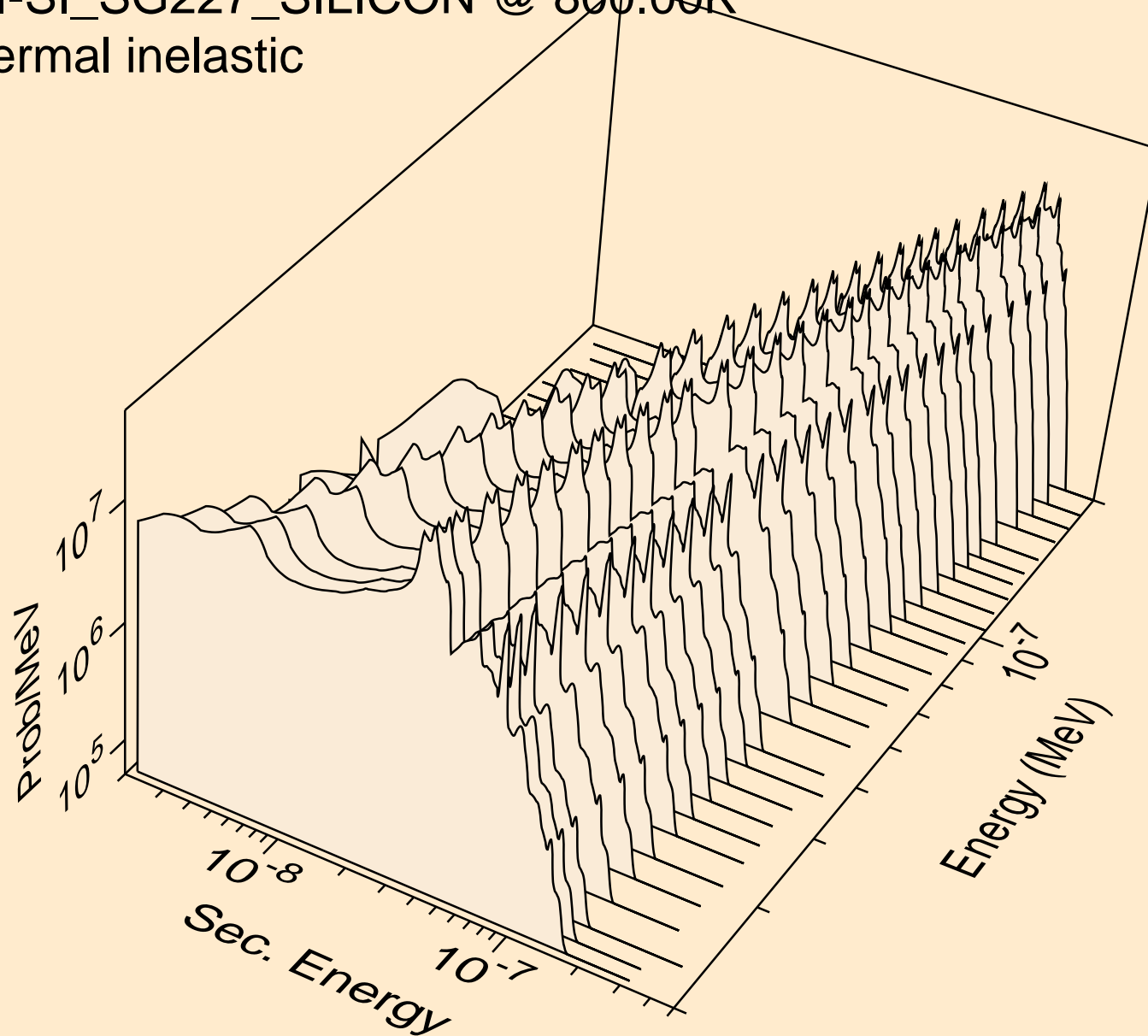
SI-SI_SG227_SILICON @ 800.00K
Thermal ebar



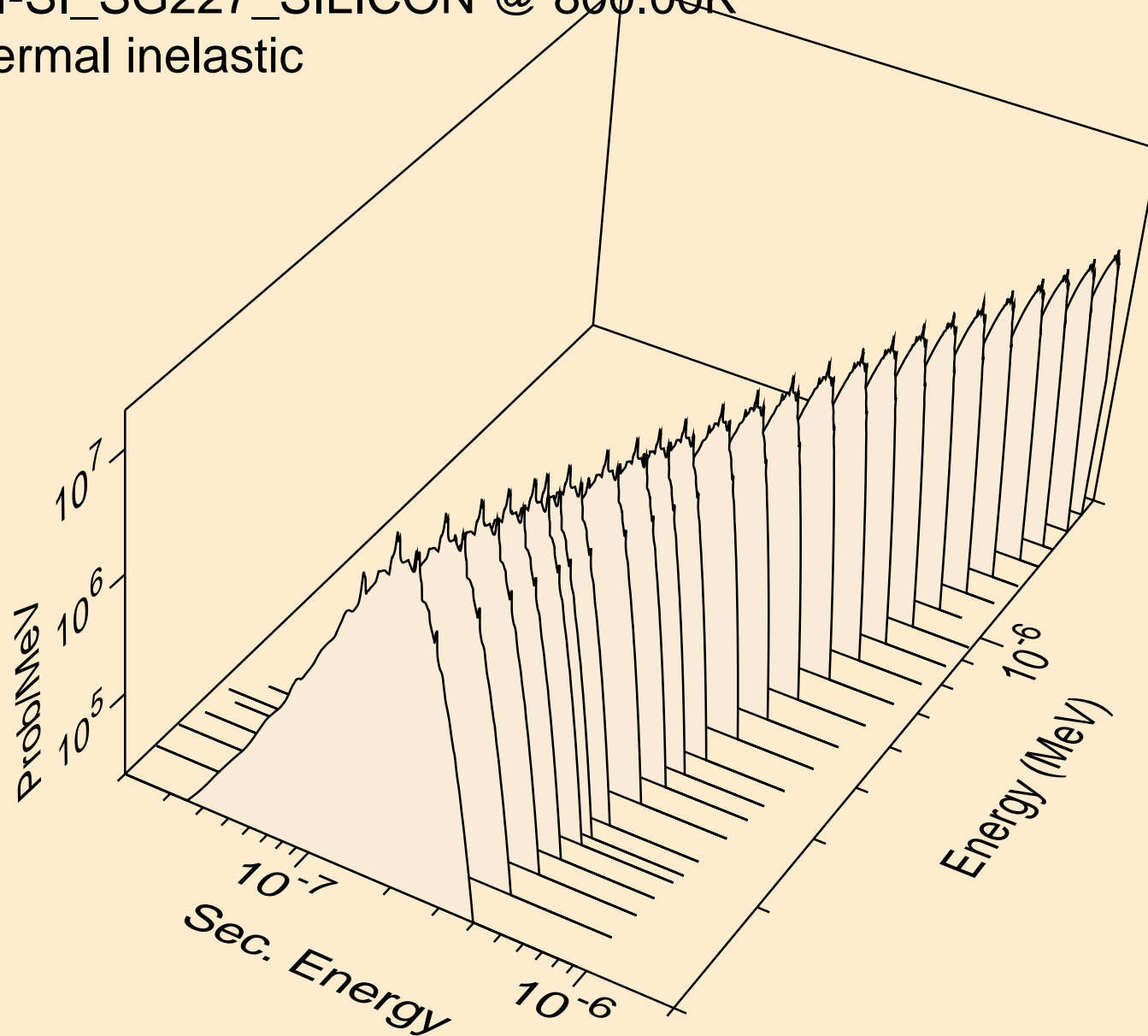
SI-SI_SG227_SILICON @ 800.00K
thermal inelastic



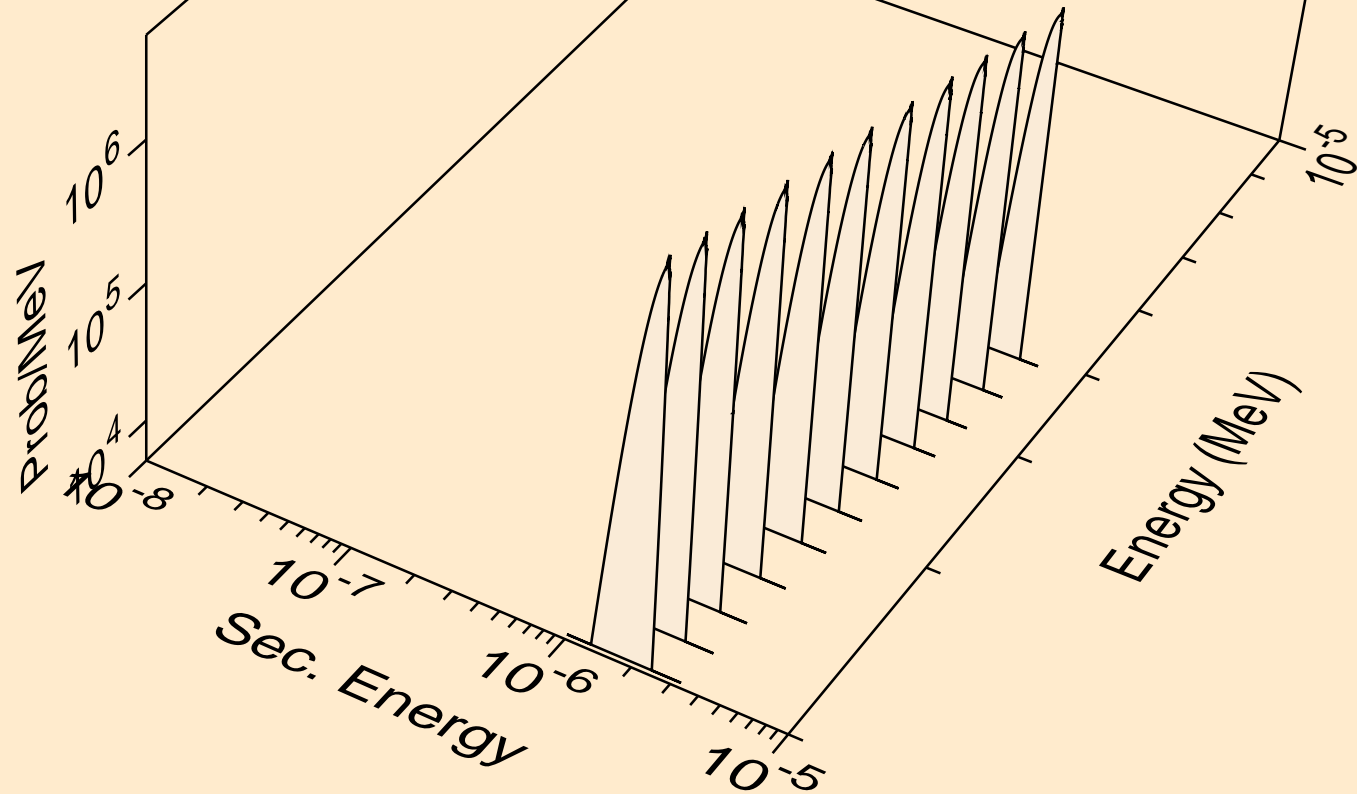
SI-SI_SG227_SILICON @ 800.00K
thermal inelastic



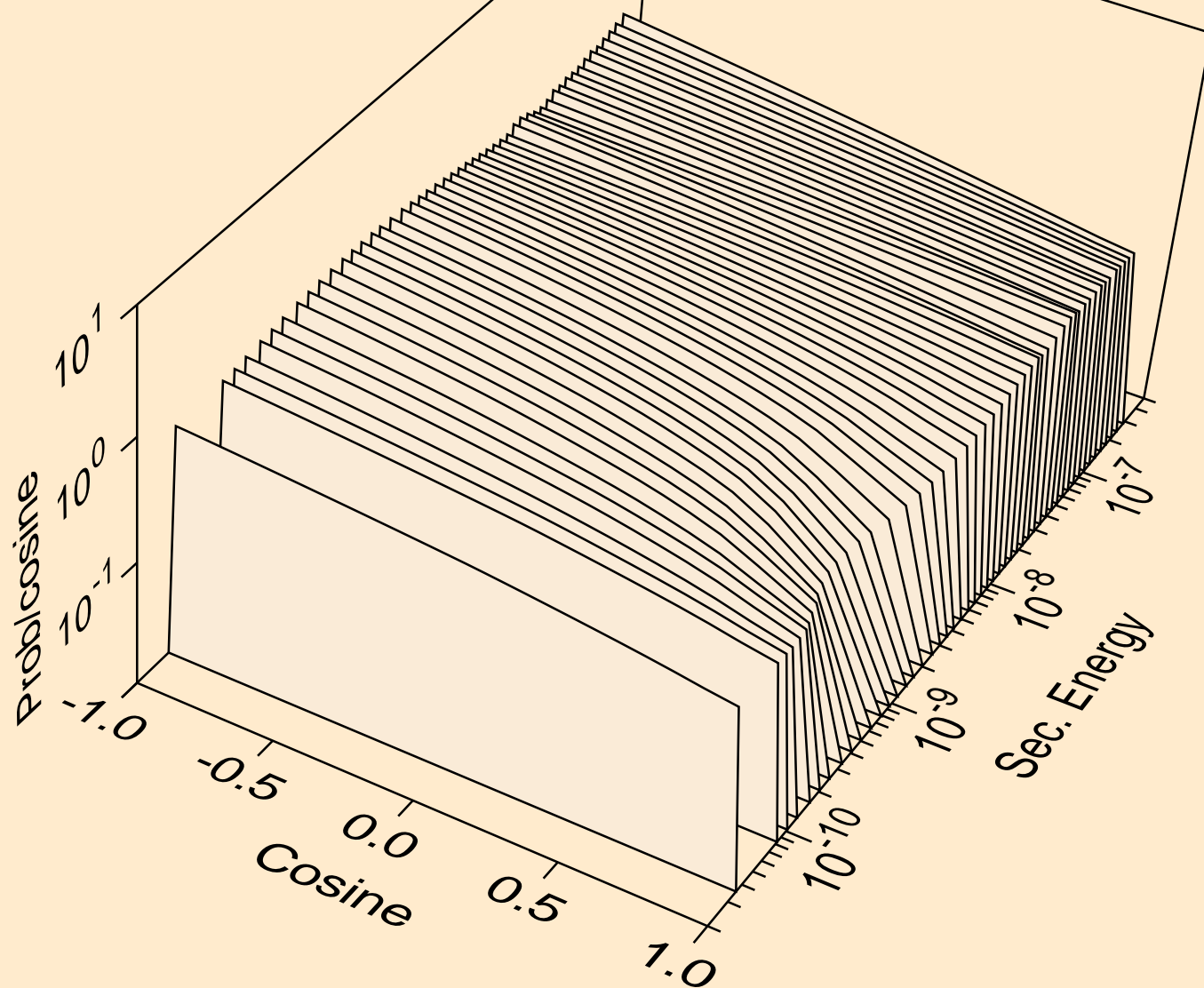
SI-SI_SG227_SILICON @ 800.00K
thermal inelastic



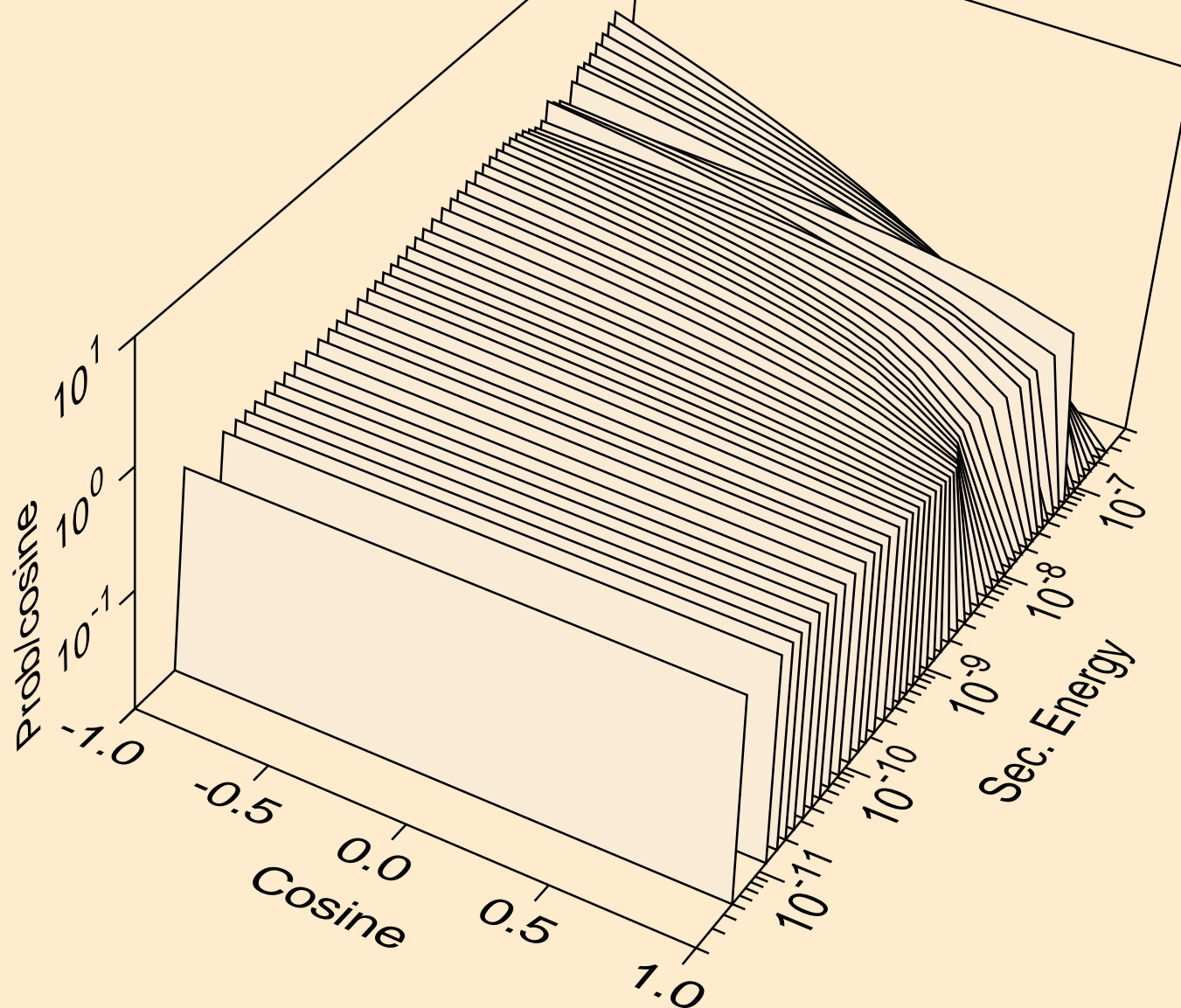
SI-SI_SG227_SILICON @ 800.00K
thermal inelastic



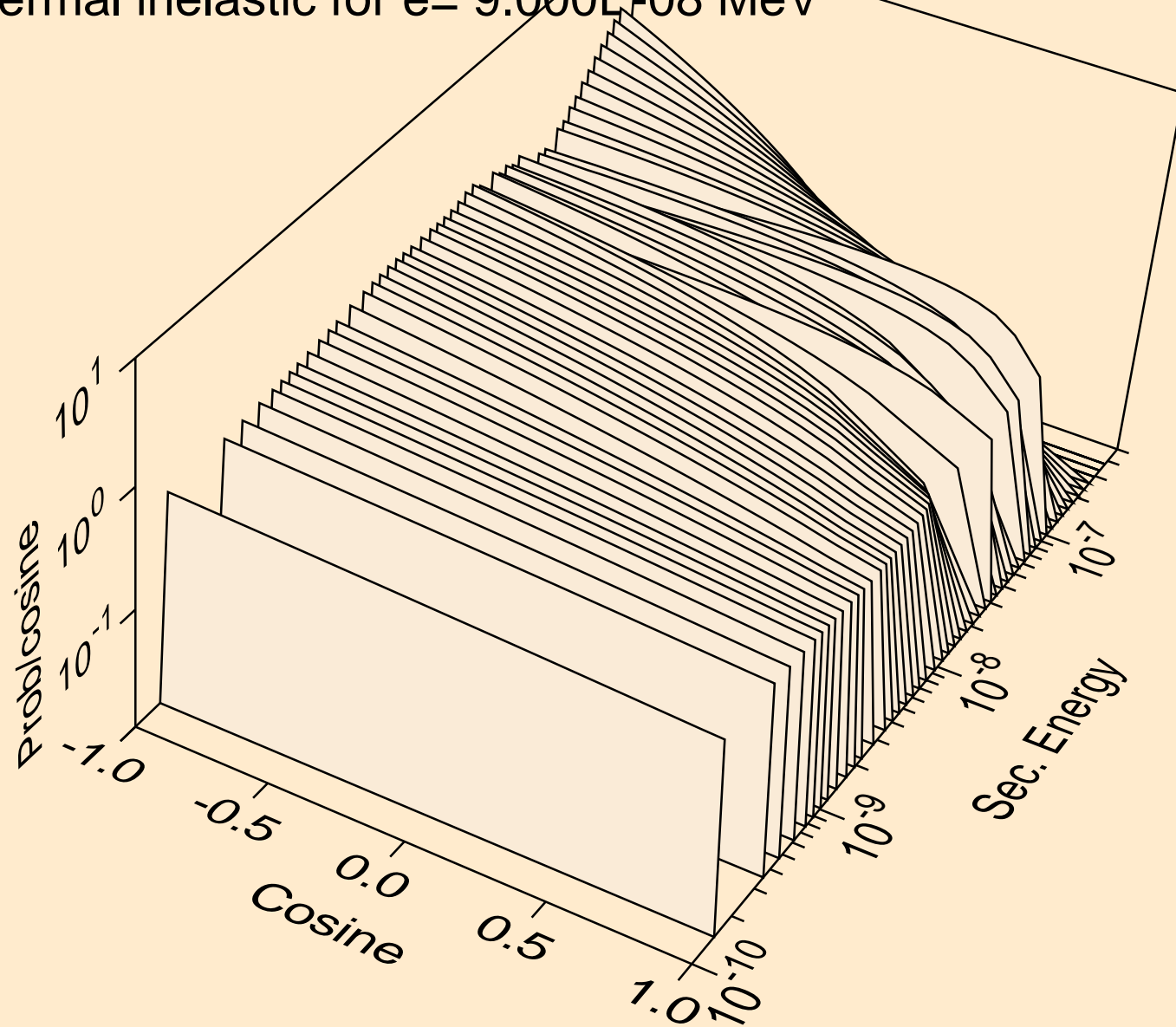
SI-SI_SG227_SILICON @ 800.00K
thermal inelastic for e= 1.012E-09 MeV



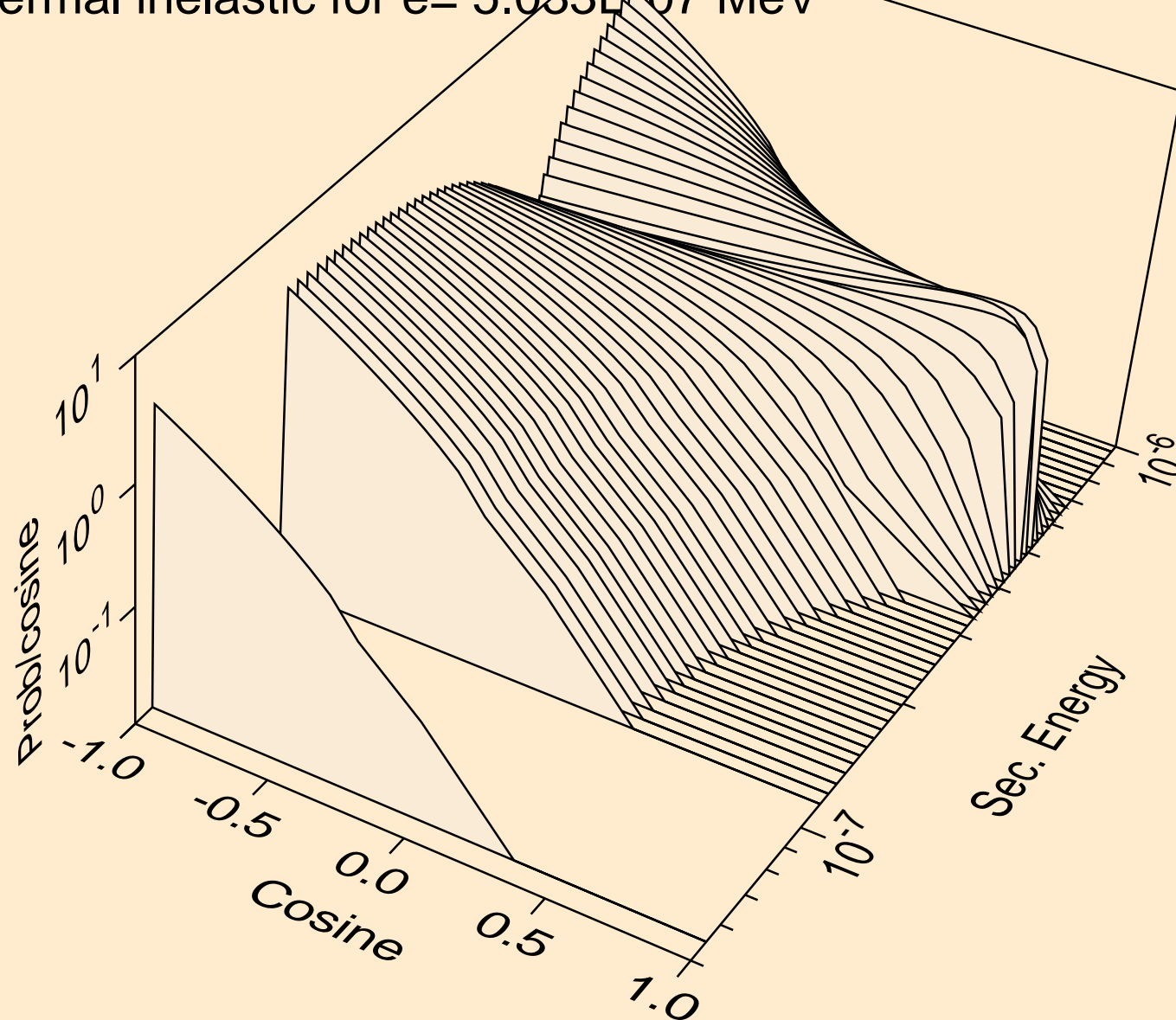
SI-SI_SG227_SILICON @ 800.00K
thermal inelastic for e= 1.417E-08 MeV



SI-SI_SG227_SILICON @ 800.00K
thermal inelastic for e= 9.000E-08 MeV



SI-SI_SG227_SILICON @ 800.00K
thermal inelastic for $e = 5.033 \times 10^{-7}$ MeV



SI-SI_SG227_SILICON @ 800.00K
thermal inelastic for e= 4.070E-06 MeV

